

**IRLR8256PbF**  
**IRLU8256PbF**

HEXFET® Power MOSFET

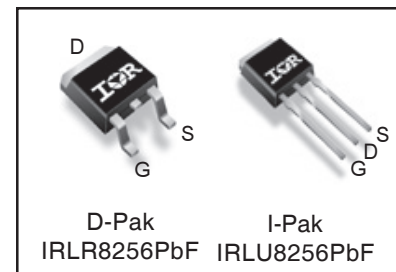
**Applications**

- High Frequency Synchronous Buck Converters for Computer Processor Power
- High Frequency Isolated DC-DC Converters with Synchronous Rectification for Telecom and Industrial Use

<b>V<sub>DSS</sub></b>	<b>R<sub>DS(on)</sub> max</b>	<b>Qg</b>
<b>25V</b>	<b>5.7mΩ</b>	<b>10nC</b>

**Benefits**

- Very Low RDS(on) at 4.5V V<sub>GS</sub>
- Ultra-Low Gate Impedance
- Fully Characterized Avalanche Voltage and Current
- Lead-Free
- RoHS compliant



<b>G</b>	<b>D</b>	<b>S</b>
Gate	Drain	Source

**Absolute Maximum Ratings**

	Parameter	Max.	Units
V <sub>DS</sub>	Drain-to-Source Voltage	25	V
V <sub>GS</sub>	Gate-to-Source Voltage	± 20	
I <sub>D</sub> @ T <sub>C</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	81 <sup>④</sup>	A
I <sub>D</sub> @ T <sub>C</sub> = 100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	57 <sup>④</sup>	
I <sub>DM</sub>	Pulsed Drain Current <sup>①</sup>	325	
P <sub>D</sub> @ T <sub>C</sub> = 25°C	Maximum Power Dissipation <sup>②</sup>	63	W
P <sub>D</sub> @ T <sub>C</sub> = 100°C	Maximum Power Dissipation <sup>②</sup>	31	
	Linear Derating Factor	0.42	W/°C
T <sub>J</sub>	Operating Junction and	-55 to + 175	°C
T <sub>STG</sub>	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

**Thermal Resistance**

	Parameter	Typ.	Max.	Units
R <sub>θJC</sub>	Junction-to-Case <sup>③</sup>	—	2.4	°C/W
R <sub>θJA</sub>	Junction-to-Ambient (PCB Mount) <sup>⑤</sup>	—	50	
R <sub>θJA</sub>	Junction-to-Ambient	—	110	

**ORDERING INFORMATION:**

See detailed ordering and shipping information on the last page of this data sheet.

Notes <sup>①</sup> through <sup>⑥</sup> are on page 11

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# IRLR/U8256PbF

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**IR** Rectifier

**Static @ T<sub>J</sub> = 25°C (unless otherwise specified)**

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV <sub>DSS</sub>	Drain-to-Source Breakdown Voltage	25	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	18	—	mV/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	4.2	5.7	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 25A ③
		—	6.7	8.5		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 20A ③
V <sub>GS(th)</sub>	Gate Threshold Voltage	1.35	1.8	2.35	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 25μA
ΔV <sub>GS(th)</sub> /ΔT <sub>J</sub>	Gate Threshold Voltage Coefficient	—	-7.2	—	mV/°C	
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	1.0	μA	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V
		—	—	150		V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -20V
g <sub>fs</sub>	Forward Transconductance	81	—	—	S	V <sub>DS</sub> = 13V, I <sub>D</sub> = 20A
Q <sub>g</sub>	Total Gate Charge	—	10	15	nC	V <sub>DS</sub> = 13V V <sub>GS</sub> = 4.5V I <sub>D</sub> = 20A See Fig. 16
Q <sub>gs1</sub>	Pre-V <sub>th</sub> Gate-to-Source Charge	—	2.3	—		
Q <sub>gs2</sub>	Post-V <sub>th</sub> Gate-to-Source Charge	—	1.6	—		
Q <sub>gd</sub>	Gate-to-Drain Charge	—	3.6	—		
Q <sub>godr</sub>	Gate Charge Overdrive	—	2.6	—		
Q <sub>sw</sub>	Switch Charge (Q <sub>gs2</sub> + Q <sub>gd</sub> )	—	5.1	—		
Q <sub>oss</sub>	Output Charge	—	9.0	—	nC	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V
R <sub>G</sub>	Gate Resistance	—	2.5	3.9	Ω	
t <sub>d(on)</sub>	Turn-On Delay Time	—	9.7	—	ns	V <sub>DD</sub> = 13V, V <sub>GS</sub> = 4.5V③ I <sub>D</sub> = 20A R <sub>G</sub> = 1.8Ω See Fig. 14
t <sub>r</sub>	Rise Time	—	46	—		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	12	—		
t <sub>f</sub>	Fall Time	—	8.5	—		
C <sub>iss</sub>	Input Capacitance	—	1470	—	pF	V <sub>GS</sub> = 0V V <sub>DS</sub> = 13V f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	453	—		
C <sub>rss</sub>	Reverse Transfer Capacitance	—	185	—		

## Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E <sub>AS</sub>	Single Pulse Avalanche Energy②	—	86	mJ
I <sub>AR</sub>	Avalanche Current ①	—	20	A
E <sub>AR</sub>	Repetitive Avalanche Energy ①	—	6.3	mJ

## Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	81④	A	MOSFET symbol showing the integral reverse p-n junction diode.
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	325		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.0	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 20A, V <sub>GS</sub> = 0V ③
t <sub>rr</sub>	Reverse Recovery Time	—	19	29	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 20A, V <sub>DD</sub> = 13V
Q <sub>rr</sub>	Reverse Recovery Charge	—	17	26	nC	di/dt = 250A/μs ③
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

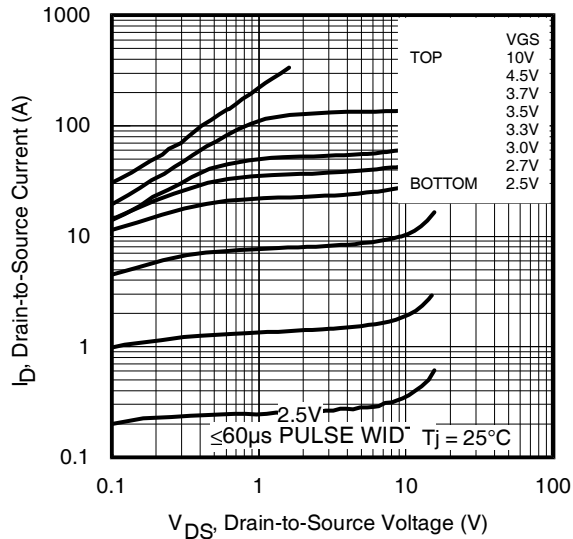


Fig 1. Typical Output Characteristics

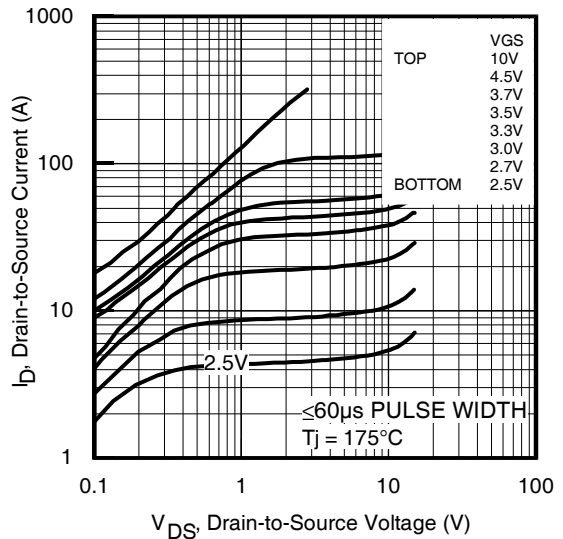


Fig 2. Typical Output Characteristics

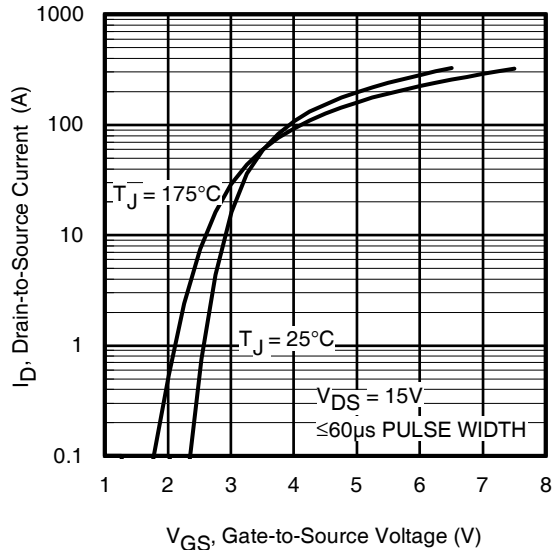


Fig 3. Typical Transfer Characteristics

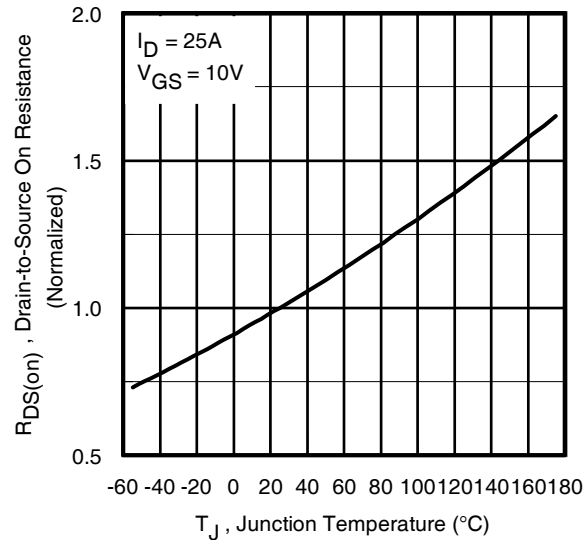
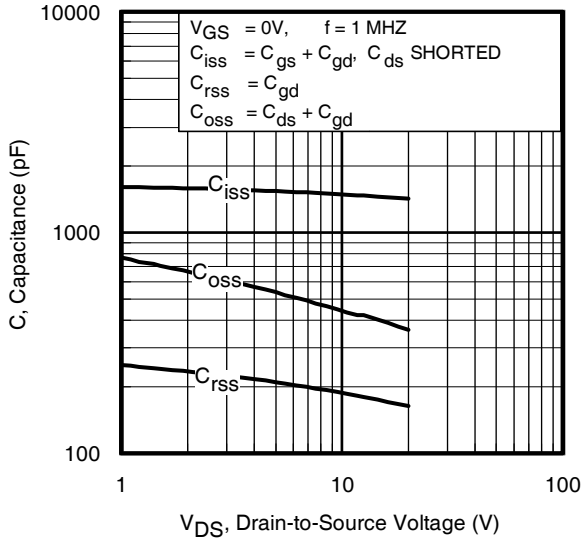
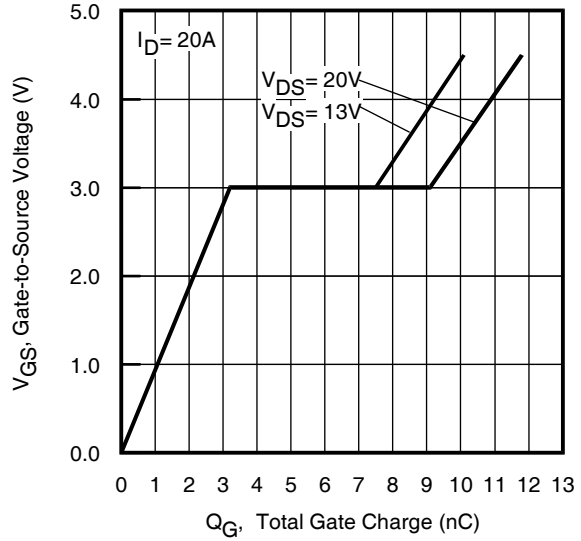


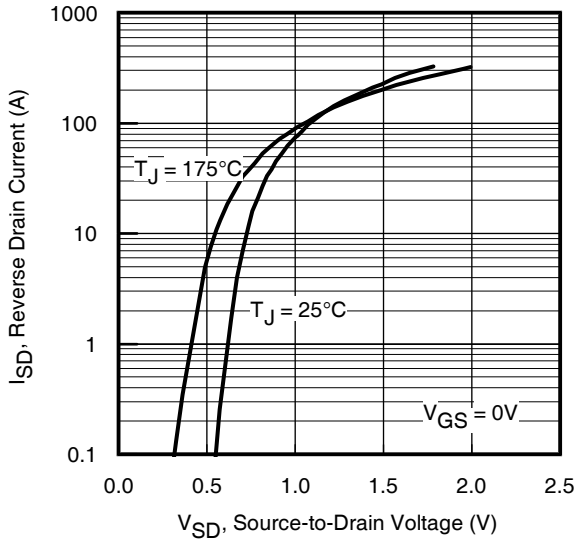
Fig 4. Normalized On-Resistance vs. Temperature



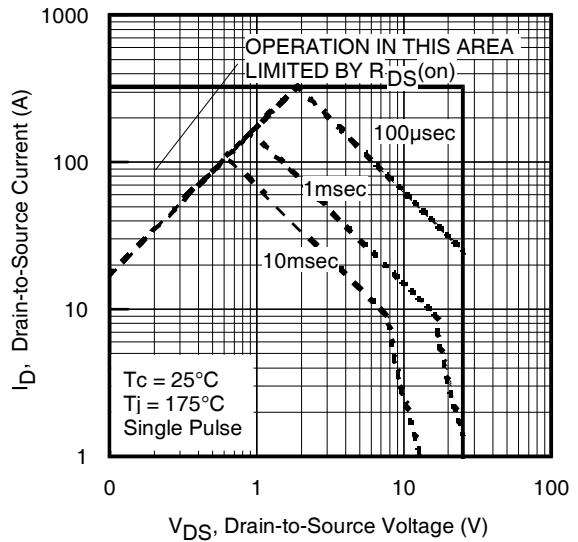
**Fig 5.** Typical Capacitance vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge vs. Gate-to-Source Voltage



**Fig 7.** Typical Source-Drain Diode Forward Voltage



**Fig 8.** Maximum Safe Operating Area

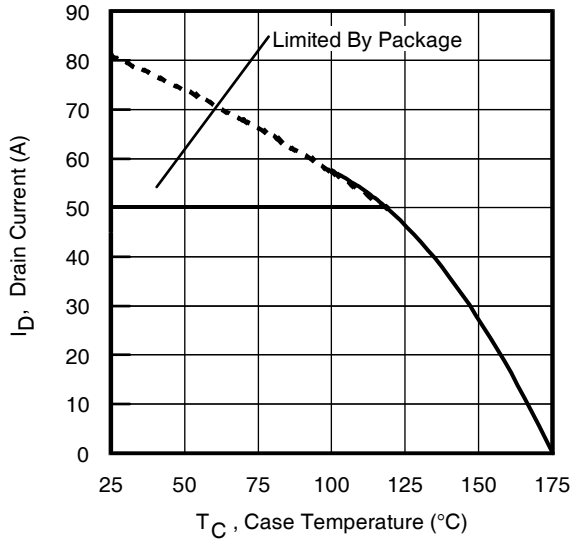


Fig 9. Maximum Drain Current vs. Case Temperature

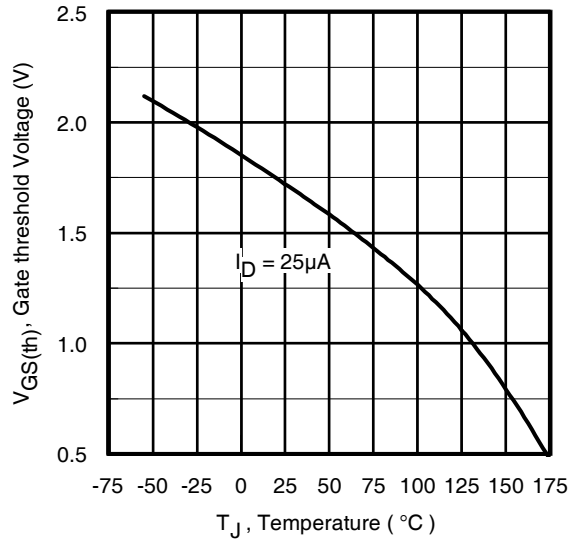


Fig 10. Threshold Voltage vs. Temperature

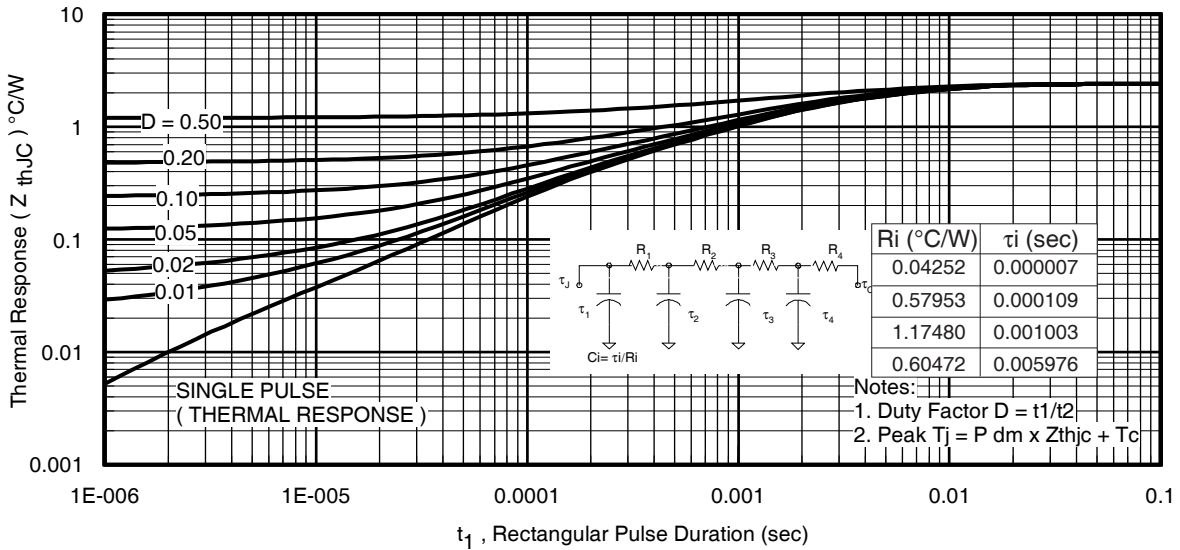
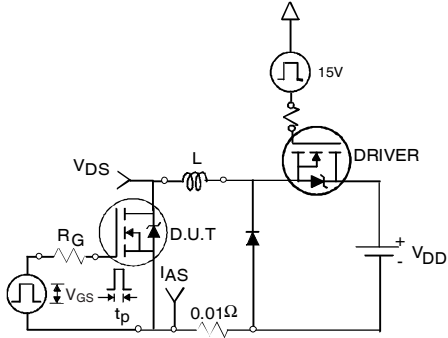


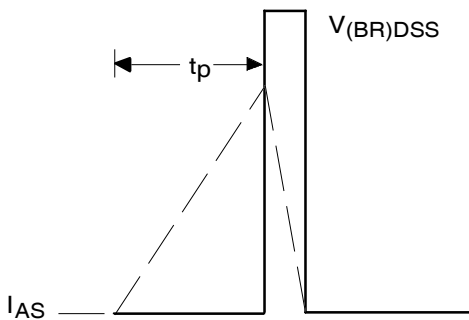
Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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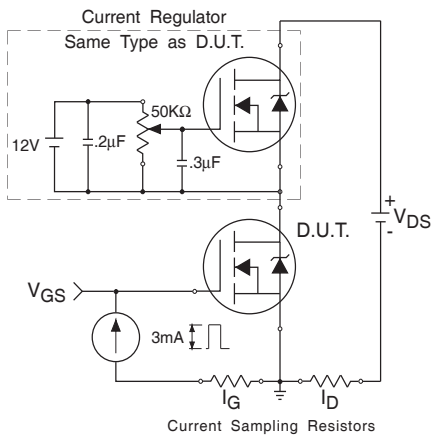
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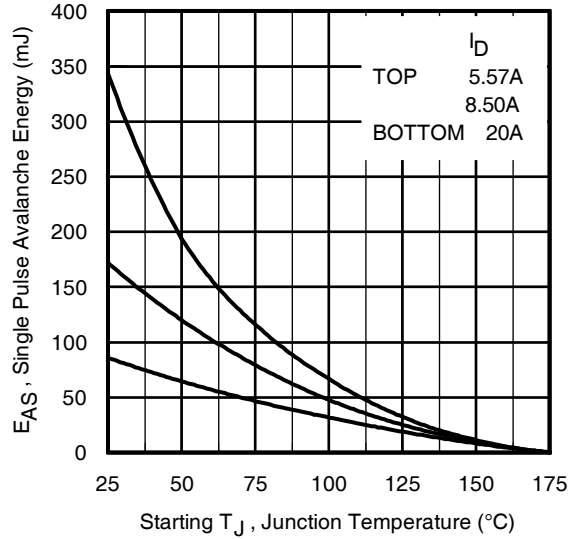
**Fig 12a.** Unclamped Inductive Test Circuit



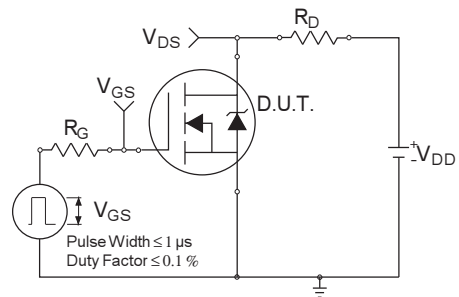
**Fig 12b.** Unclamped Inductive Waveforms



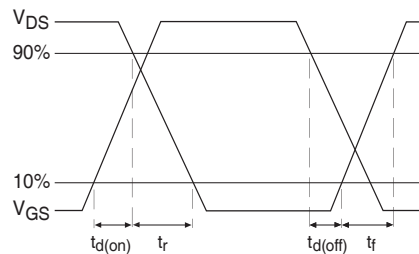
**Fig 13.** Gate Charge Test Circuit



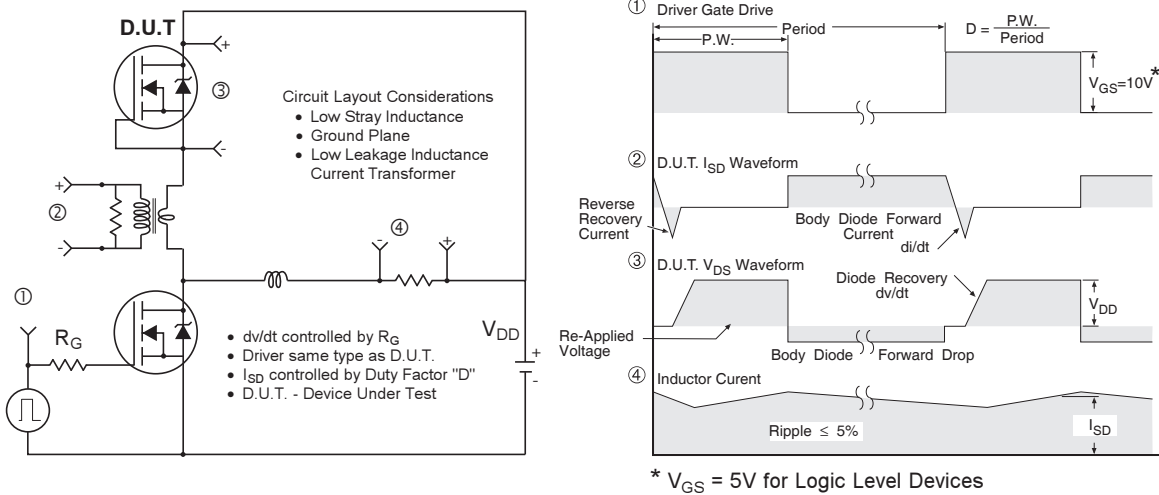
**Fig 12c.** Maximum Avalanche Energy vs. Drain Current



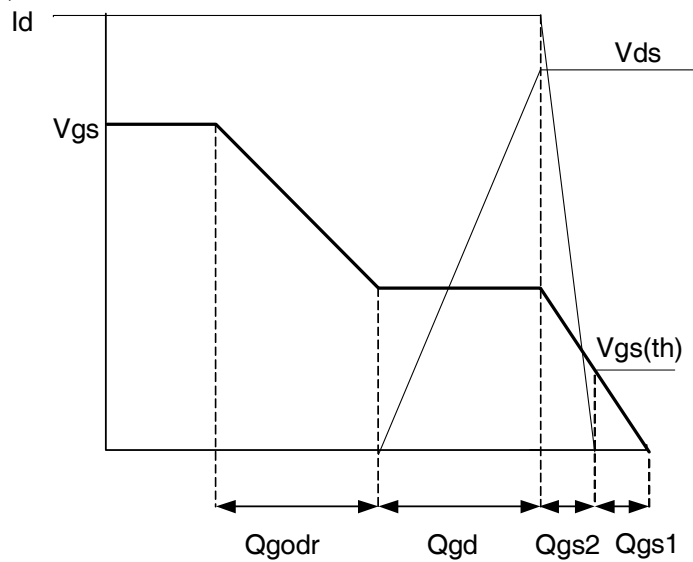
**Fig 14a.** Switching Time Test Circuit



**Fig 14b.** Switching Time Waveforms



**Fig 15. Peak Diode Recovery  $dv/dt$  Test Circuit for N-Channel HEXFET® Power MOSFETs**



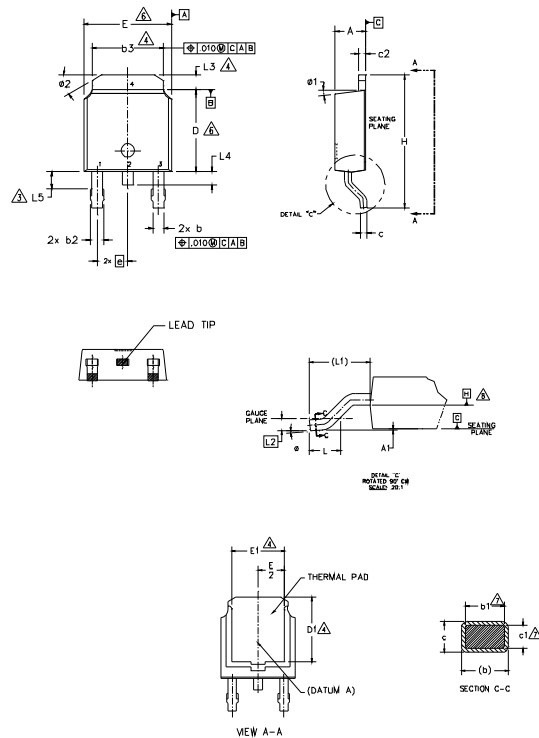
**Fig 16. Gate Charge Waveform**

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## D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
  - 2.- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS]
  - 3.- LEAD DIMENSION UNCONTROLLED IN L5.
  - 4.- DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
  - 5.- SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.10 [0.13 AND 0.25] FROM THE LEAD TIP.
  - 6.- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
  - 7.- DIMENSION b1 & c1 APPLIED TO BASE METAL ONLY.
  - 8.- DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
  - 9.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1	-	0.13	-	.005	
b	0.64	0.89	.025	.035	
b1	0.65	0.79	.025	.031	7
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	4
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	7
c2	0.46	0.89	.018	.035	
D	5.97	6.22	.235	.245	6
D1	5.21	-	.205	-	4
E	6.35	6.73	.250	.265	6
E1	4.32	-	.170	-	4
e	2.29 BSC		.090 BSC		
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74 BSC		.108 REF.		
L2	0.51 BSC		.020 BSC		
L3	0.89	1.27	.035	.050	
L4	-	1.02	-	.040	
L5	1.14	1.52	.045	.060	
Ø	0"	10"	0"	10"	
Ø1	0"	15"	0"	15"	
Ø2	25"	35"	25"	35"	

### LEAD ASSIGNMENTS

#### HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

#### IGBT & CoPAK

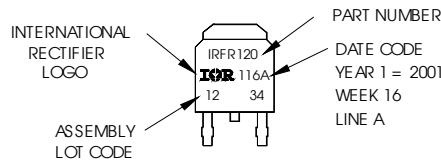
- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

## D-Pak (TO-252AA) Part Marking Information

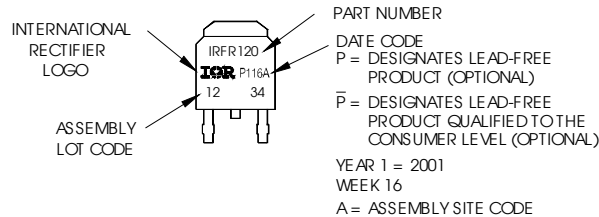
EXAMPLE: THIS IS AN IRFR120 WITH ASSEMBLY LOT CODE 1234 ASSEMBLED ON WW 16, 2001 IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position indicates "Lead-Free"

"P̄" in assembly line position indicates "Lead-Free" qualification to the consumer-level



OR

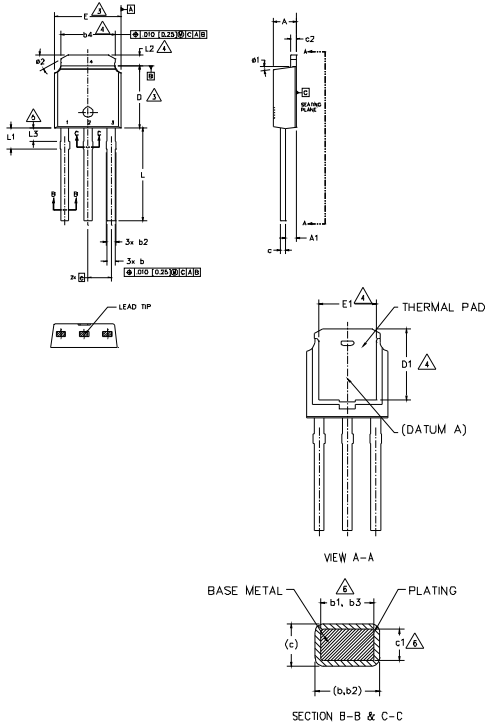


Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>



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**I-Pak (TO-251AA) Package Outline**  
 Dimensions are shown in millimeters (inches)

# IRLR/U8256PbF



- NOTES
- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
  - 2.- DIMENSION ARE SHOWN IN INCHES [MILLIMETERS]
  - 3.- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
  - 4.- THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
  - 5.- LEAD DIMENSION UNCONTROLLED IN L3.
  - 6.- DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
  - 7.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA (Date 06/02).
  - 8.- CONTROLLING DIMENSION : INCHES.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1	0.89	1.14	.035	.045	
b	0.64	0.89	.025	.035	
b1	0.65	0.79	.025	.031	6
b2	0.76	1.14	.030	.045	
b3	0.76	1.04	.030	.041	6
b4	4.95	5.46	.195	.215	4
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	6
c2	0.46	0.89	.018	.035	
D	5.97	6.22	.235	.245	3
D1	5.21	-	.205	-	4
E	6.35	6.73	.250	.265	3
E1	4.32	-	.170	-	4
e	2.29 BSC		.090 BSC		
L	8.89	9.65	.350	.380	
L1	1.91	2.29	.045	.090	
L2	0.89	1.27	.035	.050	4
L3	1.14	1.52	.045	.060	5
ø1	0	15	0	15	
ø2	25	35	25	35	

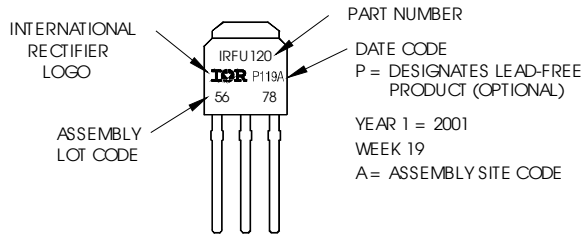
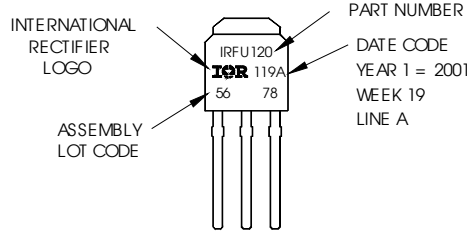
- LEAD ASSIGNMENTS
- HEXFET
- 1.- GATE
  - 2.- DRAIN
  - 3.- SOURCE
  - 4.- DRAIN

## I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120  
 WITH ASSEMBLY  
 LOT CODE 5678  
 ASSEMBLED ON WW 19, 2001  
 IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position  
 indicates Lead-Free

OR



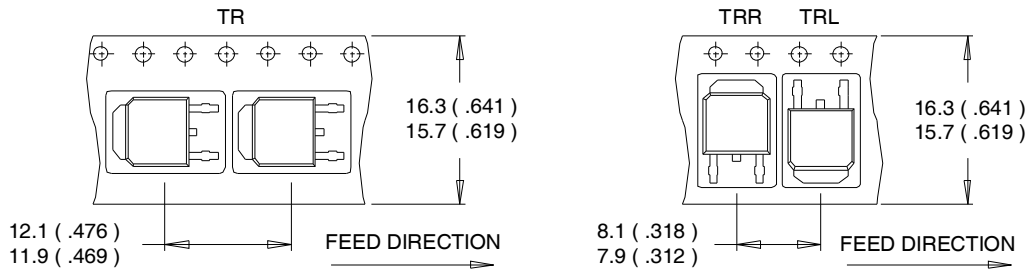
Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>  
[www.irf.com](http://www.irf.com)

# IRLR/U8256PbF

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**IR** Rectifier

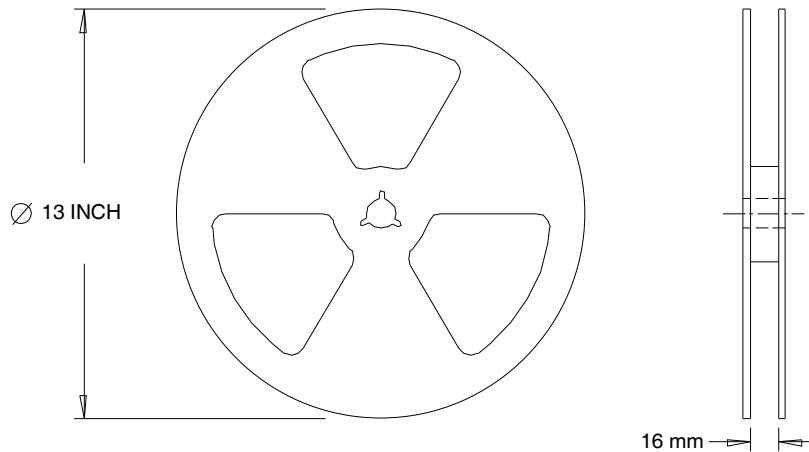
## D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



**NOTES :**

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS ( INCHES ).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



**NOTES :**

1. OUTLINE CONFORMS TO EIA-481.

**Note:** For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Orderable part number	Package Type	Standard Pack		Note
		Form	Quantity	
IRLR8256PBF	D-PAK	Tube/Bulk	75	
IRLR8256TRPBF	D-PAK	Tape and Reel	2000	
IRLR8256PBF	I-PAK	Tube/Bulk	75	

### Qualification Information<sup>†</sup>

Qualification level	Industrial <sup>††</sup>	
	(per JEDEC JESD47F <sup>†††</sup> guidelines)	
	Comments: This family of products has passed JEDEC's Industrial qualification. IR's Consumer qualification level is granted by extension of the higher Industrial level.	
Moisture Sensitivity Level	D-PAK	MSL1 (per JEDEC J-STD-020D <sup>†††</sup> )
	I-PAK	Not applicable
RoHS Compliant	Yes	

† Qualification standards can be found at International Rectifier's web site <http://www.irf.com/product-info/reliability>

†† Higher qualification ratings may be available should the user have such requirements. Please contact your International Rectifier sales representative for further information: <http://www.irf.com/whoto-call/salesrep/>

††† Applicable version of JEDEC standard at the time of product release.

### Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.43\text{mH}$ ,  $R_G = 25\Omega$ ,  $I_{AS} = 20\text{A}$ .

③ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

④ Calculated continuous current based on maximum allowable junction temperature.

Package limitation current is 50A.

⑤ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.

⑥  $R_\theta$  is measured at  $T_J$  approximately  $90^\circ\text{C}$ .

Data and specifications subject to change without notice.

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